

The word "Omega" is written in a large, black, cursive font. A red outline of the Greek letter Omega symbol is positioned behind the letter 'O'.

OMEGAPIX

The first 3D IC prototype for the
ATLAS upgrade SLHC pixel project
designed at LAL

École IN2P3 de microélectronique
La Londe les Maures
12/15 octobre 2009

A. Lounis, C. de La Taille, N. Seguin-Moreau,
G. Martin-Chassard, D. Thienpont from LAL (Orsay)
and Y. Guo from LPNHE (Paris)

A red outline of the Greek letter Omega symbol is positioned behind the word "Orsay".

Orsay MicroElectronic Group Associated

- Chartered/Tezzaron 3D technology for the ATLAS upgrade SLHC pixel project
- Analog cell design: analog tier
 - Preamplifier
 - Shaper + Threshold DAC
 - Discriminator
- Digital cell design: digital tier
 - 24 DFF shift register
- Dedicated test chip
- Conclusion

SLHC : 10x increased luminosity => new RO electronics have to be designed

We are studying an alternative approach to:

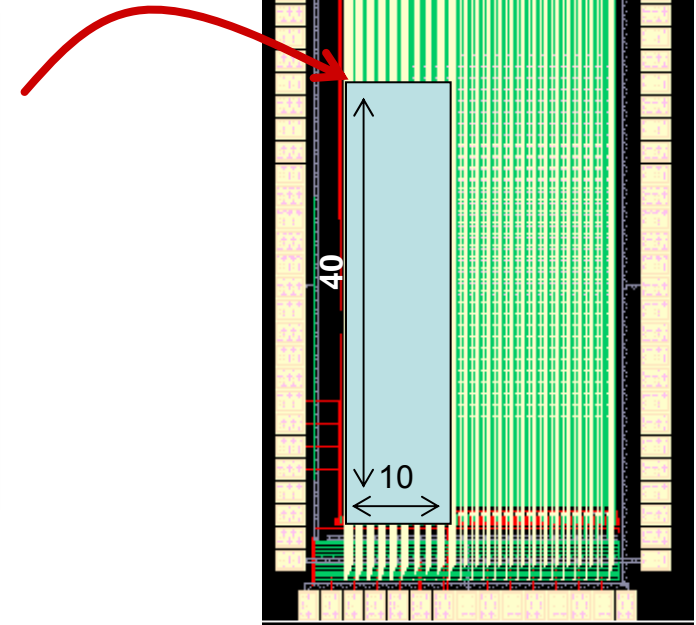
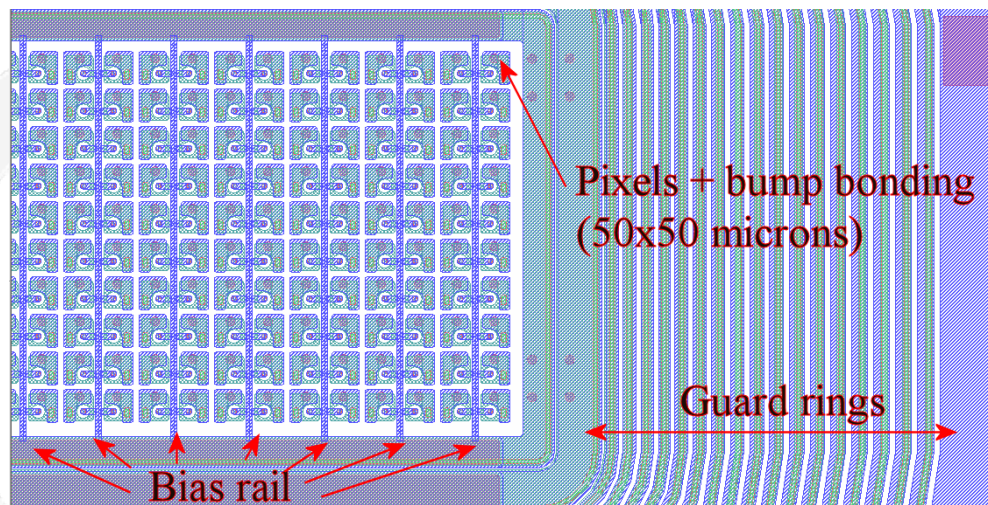
- ✓ Minimize pixel pitch: study smaller pixels ($50 \times 50 \mu\text{m}^2$ instead of $50 \times 250 \mu\text{m}^2$)
- ✓ Target $3 \mu\text{W}/\text{ch}$: $2 \mu\text{W}/\text{ch}$ for the analogue tier, $1 \mu\text{W}/\text{ch}$ for the digital one
- ✓ Design analogue tier with low noise low power preamp including shaping + threshold DAC
- ✓ Low threshold ($1000 e^-$), low noise ($100 e^-$)
- ✓ Discriminator in digital tier + dynamic memory

Goals:

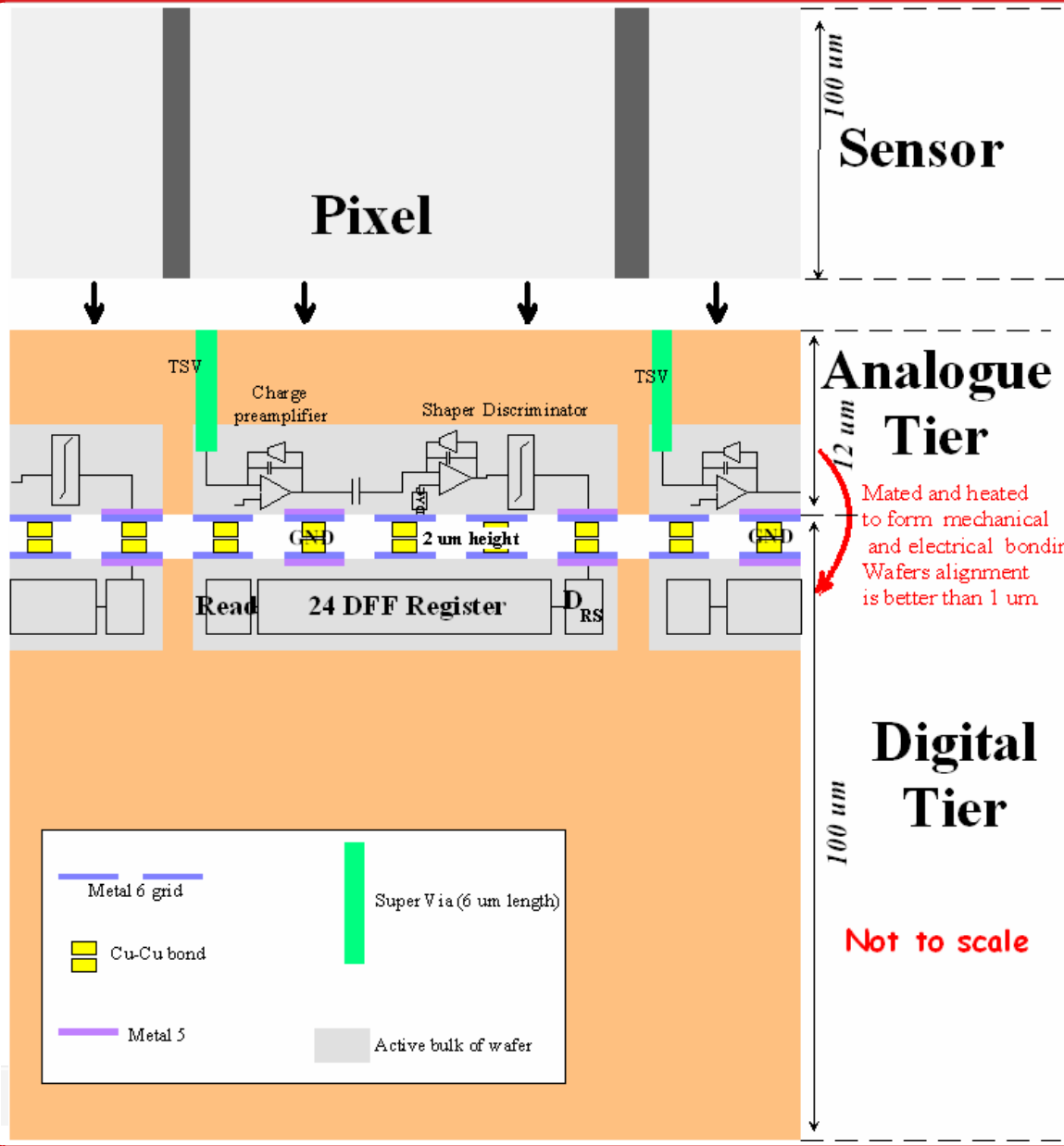
- ✓ Explore the Chartered 130nm CMOS techno and 3D features from Tezzaron
- ✓ Study variants of blocks for FEI4 (preamp, discri, DAC, local storage...)
- ✓ Study digital coupling to analog tier with discri in digital tier (**not still implemented**)

Plannar pixel sensor designed at MPI (Munich)

- ✓ n⁺ pixels on p-type substrate
- ✓ 6,85 x 3,26 mm²
- ✓ 400 pixels
- ✓ 50 x 50 μm²
- ✓ 18 GRs
- ✓ thickness: ~ 100 μm but 75 μm expected at term



OMEGAPIX: first 3D IC prototype



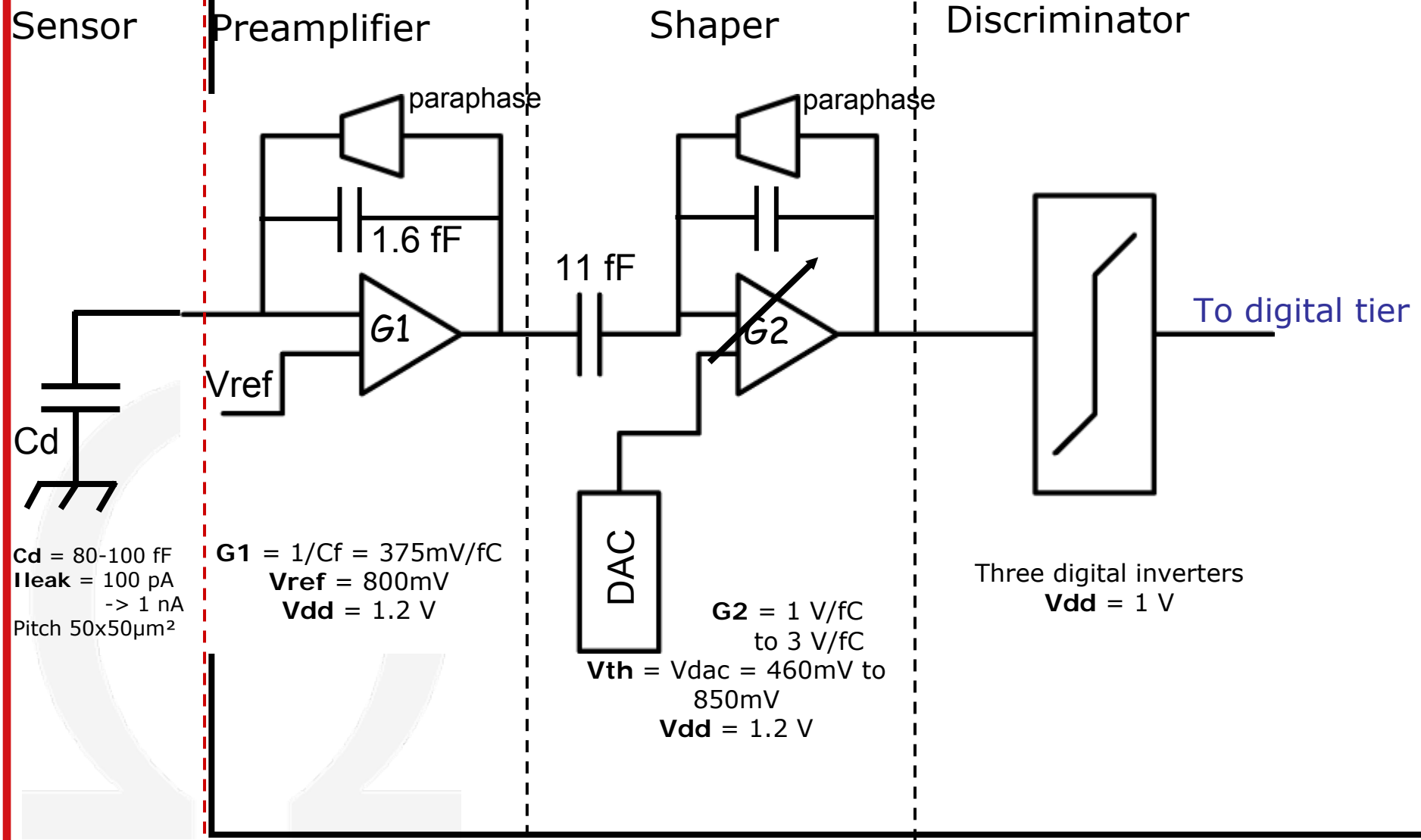
OMEGAPIX is a two stacks 3D chip: analogue tier + digital tier. Sensor will be bonded directly on the back side of the thinned analogue layer.

Analogue channel: preamplifier + shaper + discriminator + DAC to fix the threshold

Digital channel: one 24 DFlipflop register

OMEGAPIX includes 1536 channels divided in 24 columns and 64 ch/col.

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OMEGAPIX: Analogue tier – Charge preamplifier *Omega*

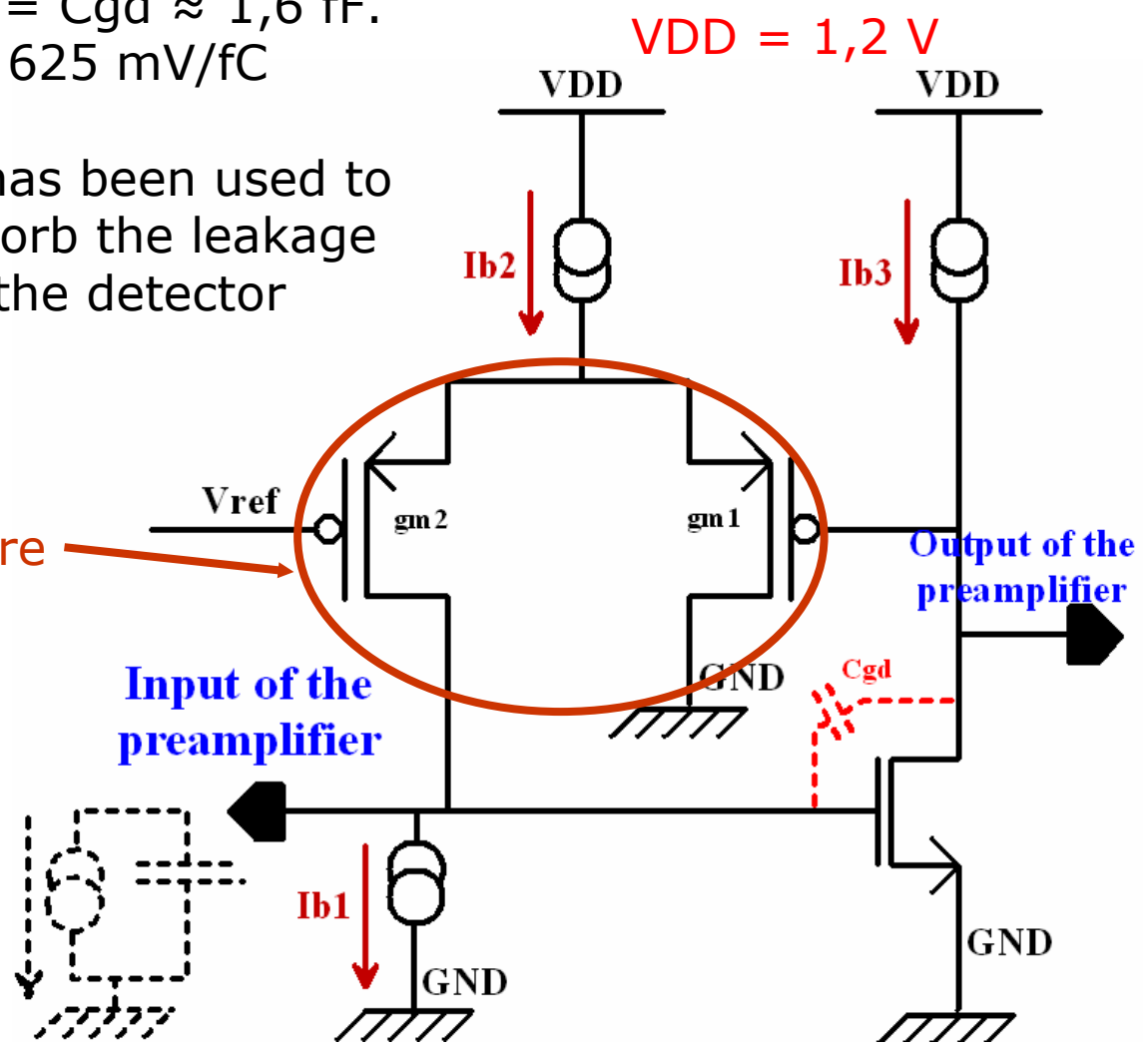
✓ Parasitic capacitance C_{gd} performs the feedback capacitance: $C_f = C_{gd} \approx 1,6 \text{ fF}$.
 Ideal gain is $1/C_f \rightarrow 625 \text{ mV/fC}$

✓ A **paraphase** structure has been used to fix the DC points and absorb the leakage current coming from the detector

Paraphase structure

$I_{b1} = 100 \text{ pA}, I_{b2} = 2 \text{ nA}, I_{b3} = 1 \text{ }\mu\text{A}$

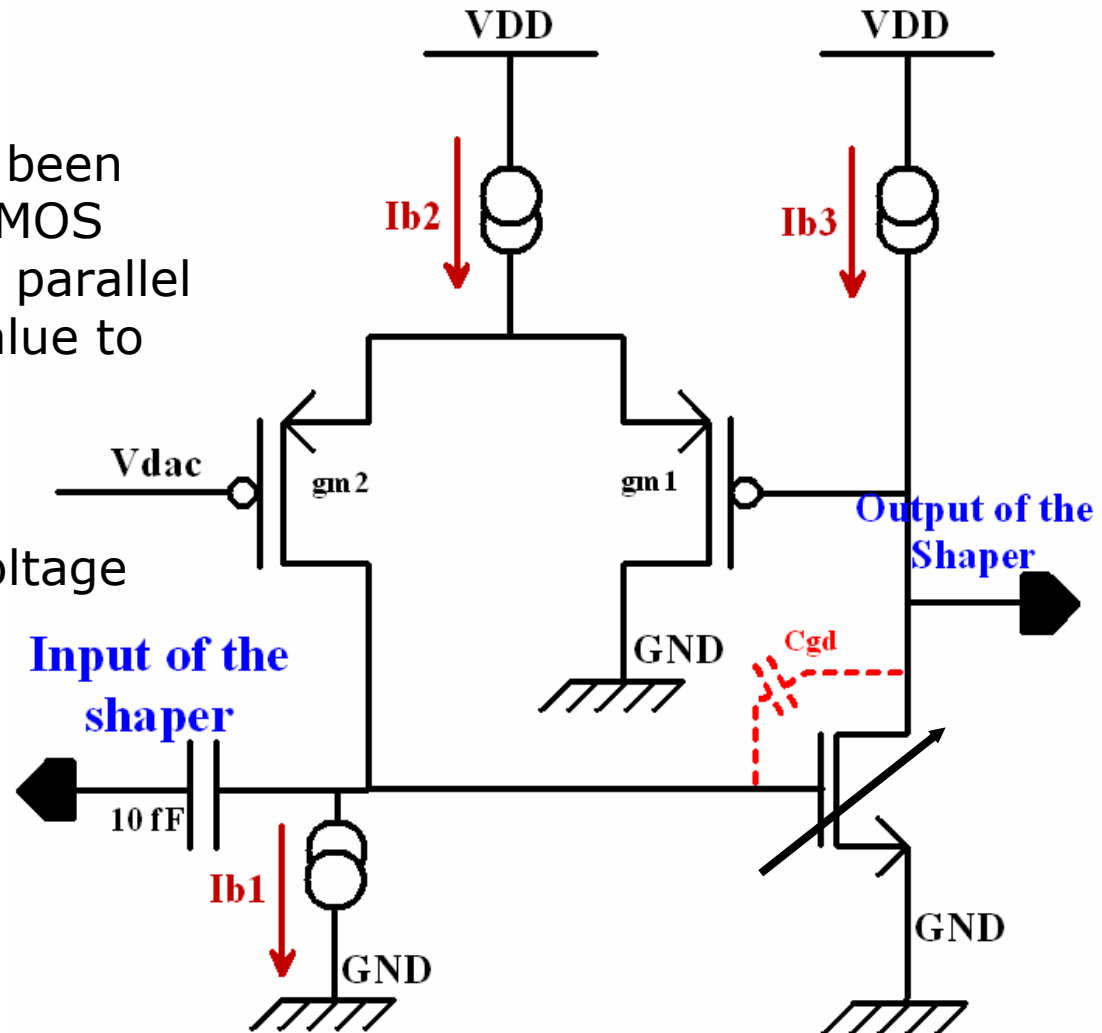
$R_{eq} = 180 \text{ M}\Omega$ if $I_{b1} = 100 \text{ pA}$
 $R_{eq} = 74 \text{ M}\Omega$ if $I_{b1} = 1 \text{ nA}$



$I_{b1} = 2.5 \text{ nA}$, $I_{b2} = 5 \text{ nA}$, $I_{b3} = 50 \text{ nA}$

A shaper variable gain has been designed; four different NMOS transistors can be switched in parallel which leads to make C_{gd} value to vary

DAC fixes the output DC voltage



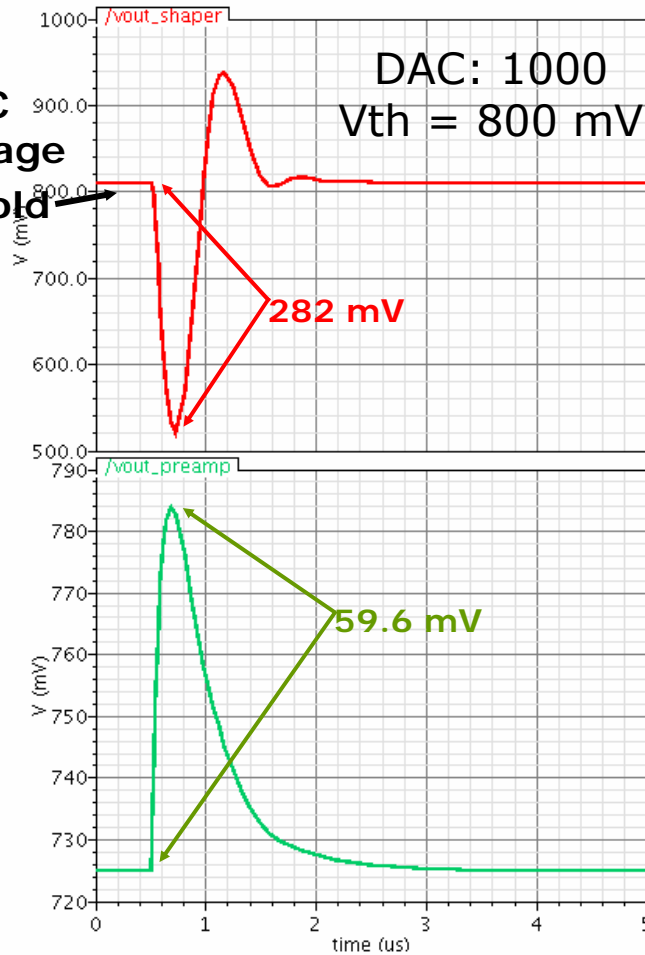
OMEGAPIX: typical simulation

Simulation conditions: $Q_{inj} = 1000 e^-$
DAC: 1000 (only 2.5/0.5 nmos_1p5_lvt as shaper), $V_{th} = 800 mV$

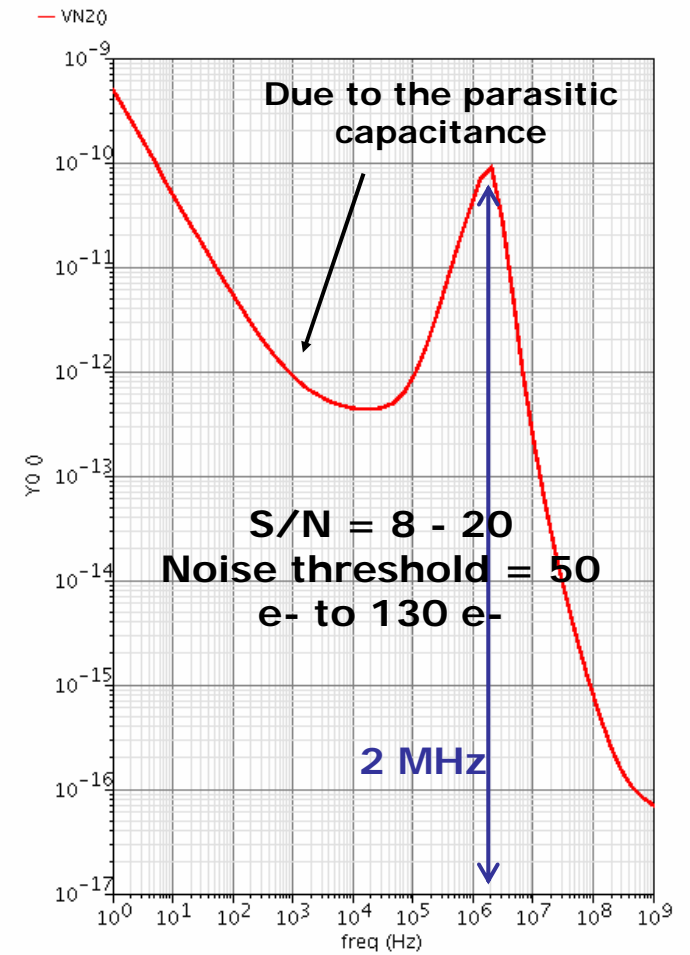
Shaper
DAC fixes the DC shaper output voltage and so the threshold

Preamplifier
 $V_{max} = Q/C \Rightarrow 60 mV$

Transient response



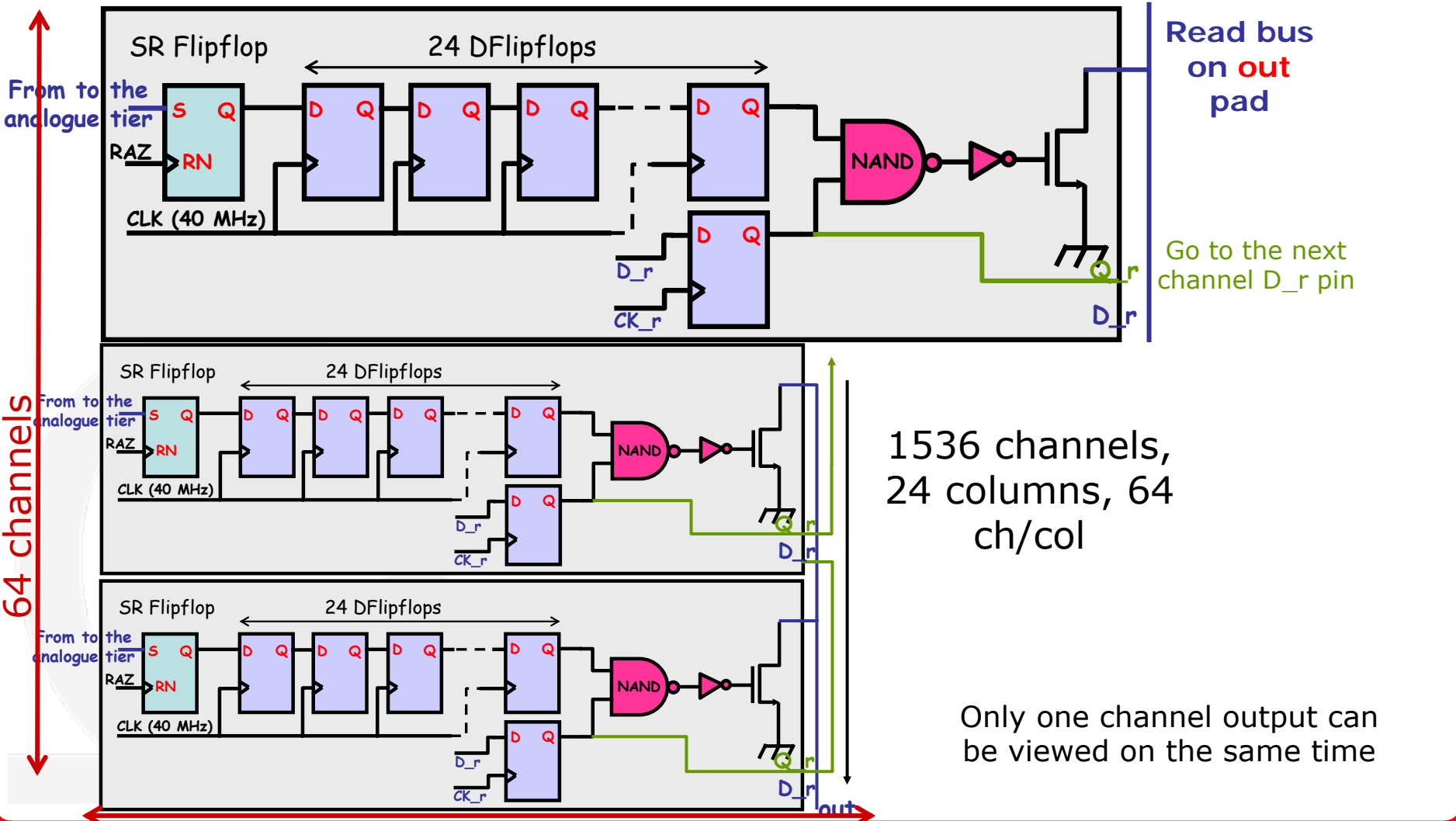
Noise at the output of the shaper



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OMEGAPIX: Digital tier

Digital tier has been designed by **Yixian Guo** from LPNHE.
Each channel includes a 24 DFlipflop register: main tests will focus about the noise study

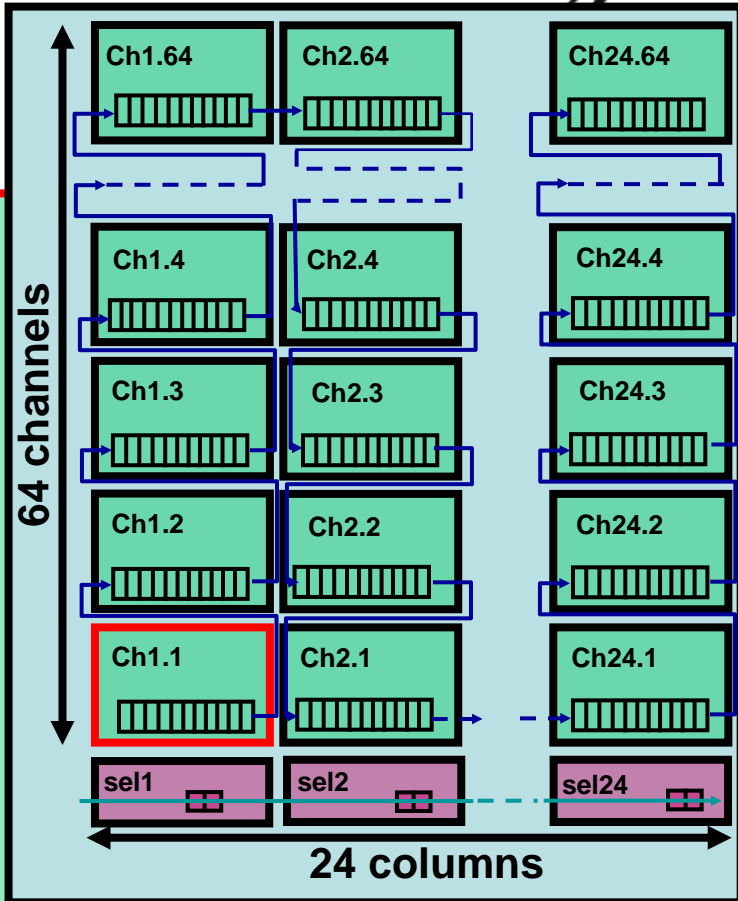
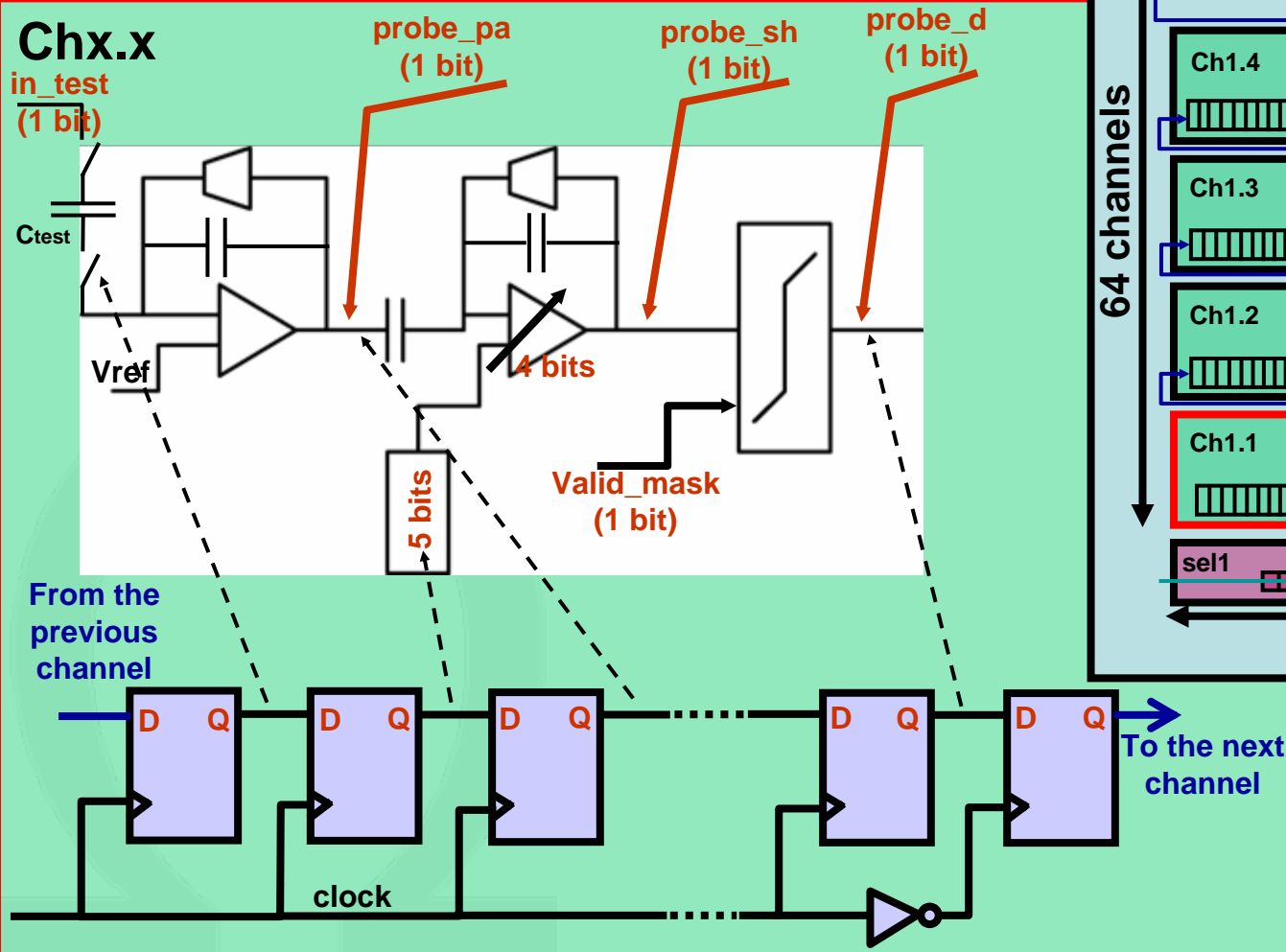


24 columns

- Chartered/Tezzaron 3D technology for the ATLAS upgrade SLHC pixel project
- Analog cell design: analog tier
 - Preamplifier
 - Shaper + Threshold DAC
 - Discriminator
- Digital cell design: digital tier
 - 24 DFF shift register
- **Dedicated test chip**
- Conclusion

OMEGAPIX: dedicated test chip - Slow Control

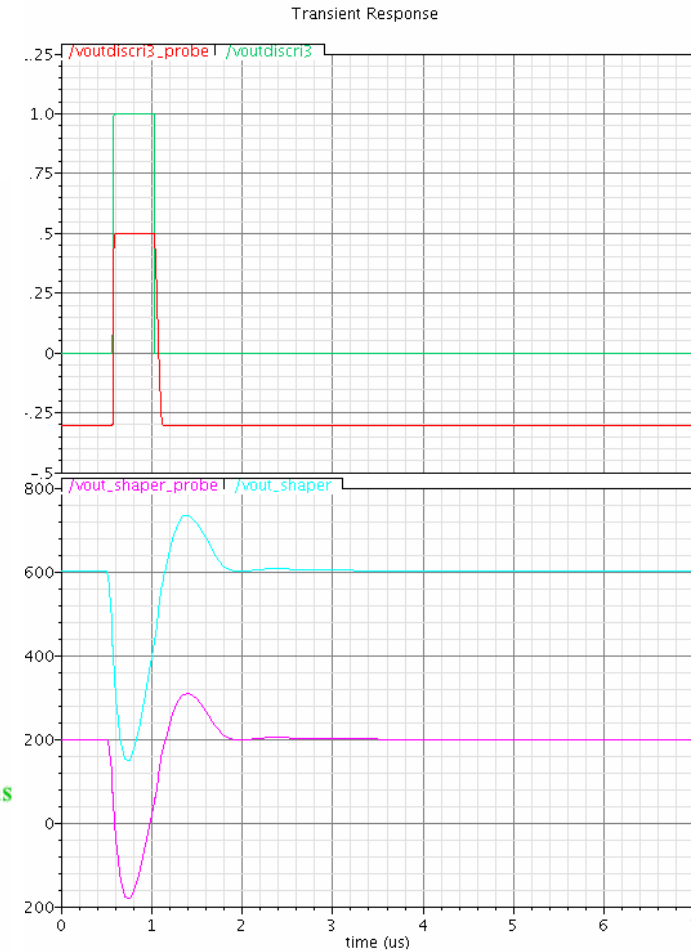
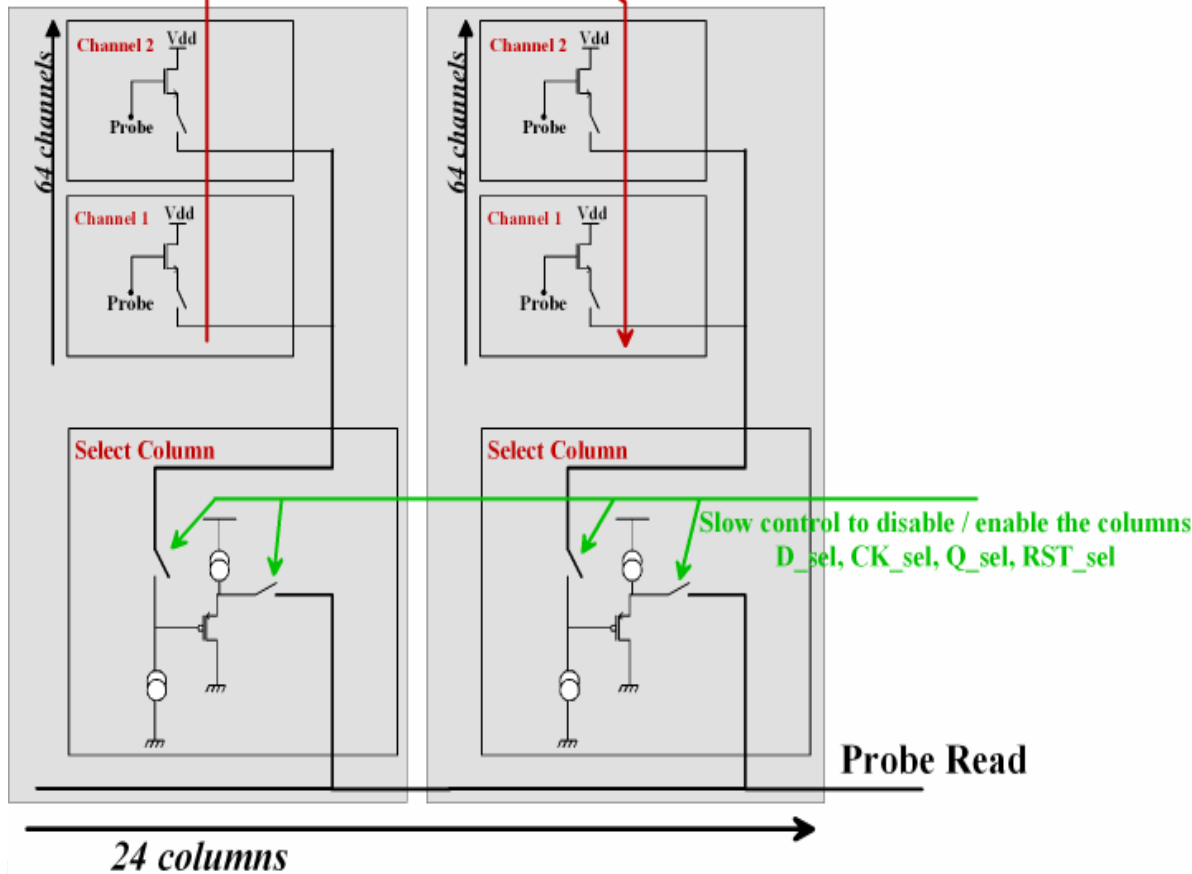
24 columns, 64 channels/columns -> 1536 channels
14 SC bits/channel -> 21504 SC bits
2 SC bits/selectColumn -> 48 bits



- In_test -> 1 bit
 - 3 probes: preamplifier, shaper, discriminator -> 3 bits
 - DAC -> 5 bits
 - Shaper: variable gain -> 4 bits
 - Discriminator: mask -> 1 bit
- > 14 SC bits / channel

One channel can be viewed on the same time

One Slow Control for the channel configuration
D_SC, CK_SC, Q_SC, RST_SC



Several column types have been designed allowing us to study various flavours of transistor types (normal, low VT, 3p3), noise, oscillations...

- ✓ Columns 1 to 10: reference channels
- ✓ Columns 11 to 18: various preamplifier transistor types have been integrated
- ✓ Column 19 to 22: without variable gain
- ✓ Column 23: discriminator has been removed
- ✓ Column 24: shaper has been removed

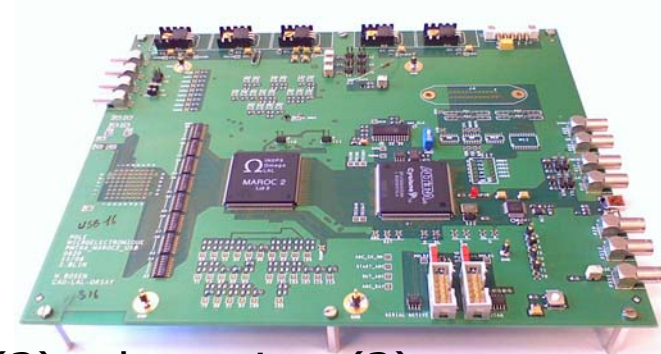
At the first time, the sensor will not be bonded, nevertheless there is the possibility to inject charge via a pad

Some others possibilities are available...

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 - 24 DFF shift register
- Dedicated test chip
- **Conclusion**

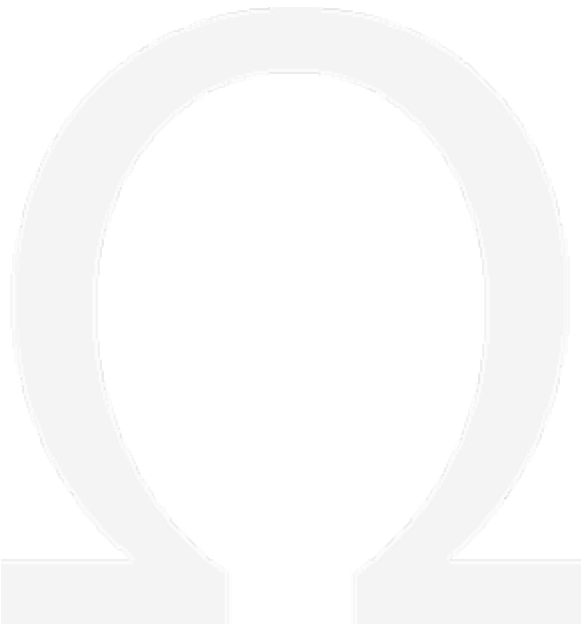
Measurements

- ✓ Technology characterization: measurements of various transistor types, noise, layers coupling, radiation hardness
- ✓ At first, tests will be performed without sensor (test board and Software OK), then with the Munich planar pixel prototype (test board to be defined)



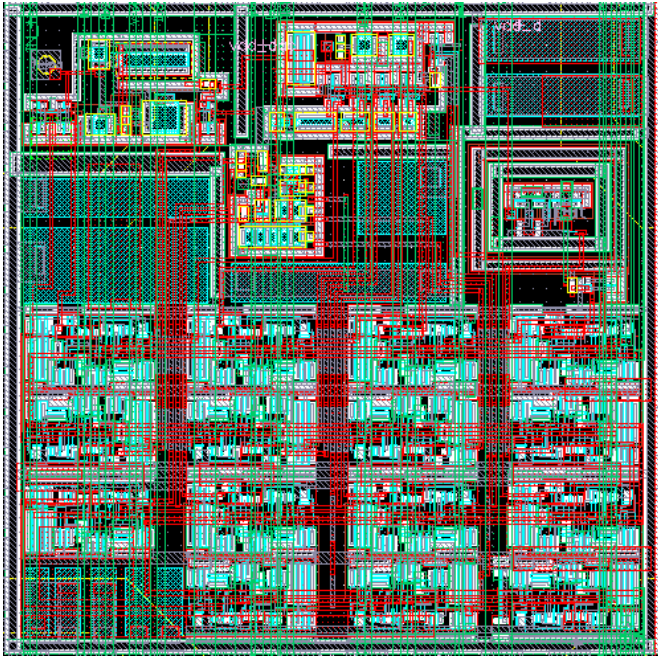
Up-coming design

- ✓ Digital tier with the readout system: TOT (?), clustering (?)
- ✓ Analogue tier finalization and optimization



Layout: some pictures...

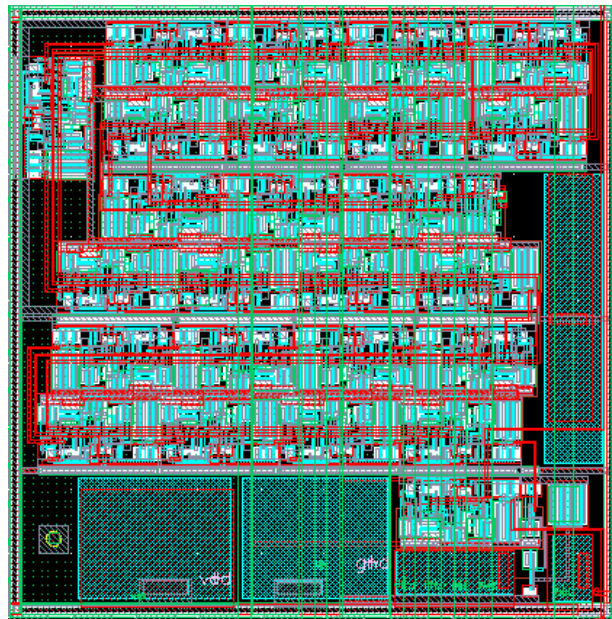
One channel: analogue part



50 μm

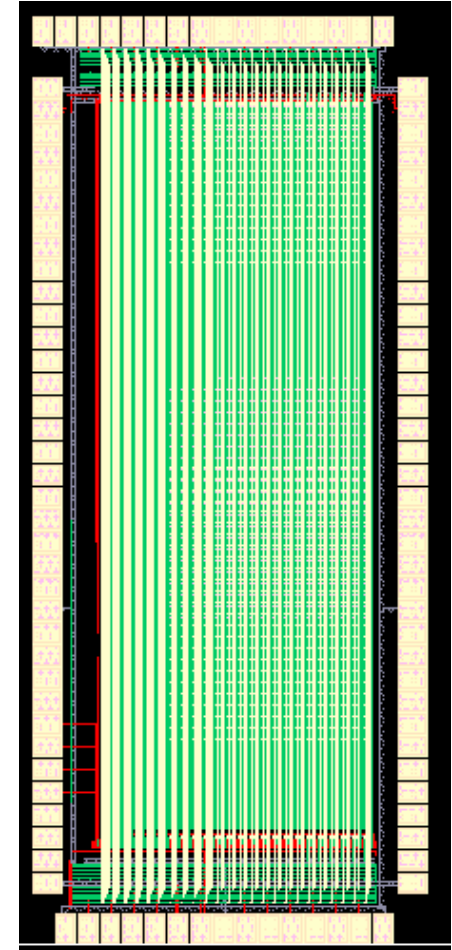
4 mm

One channel: digital part



50 μm

1,74 mm



Entire analogue tier

VITESSE: a new international consortium for development of **Vertical Integrated Technologies for Electronics and Silicon SENSORS** (3D), gathers 15 institutes

- Fermilab (Batavia) and LBNL (Berkeley) in USA
- 6 IN2P3 laboratories (France) in particular LAL Orsay
- 6 Italian institutes
- University of Bonn (Germany)
- AGH University of Science & Technology (Poland)

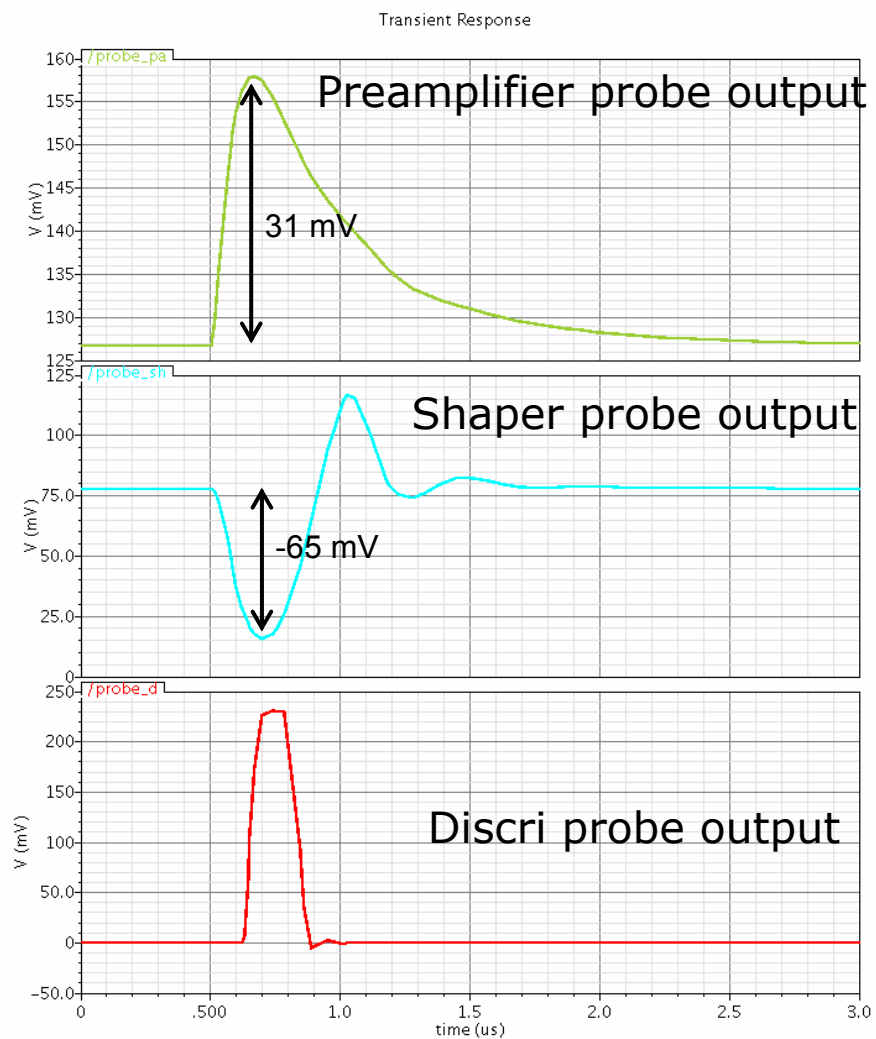
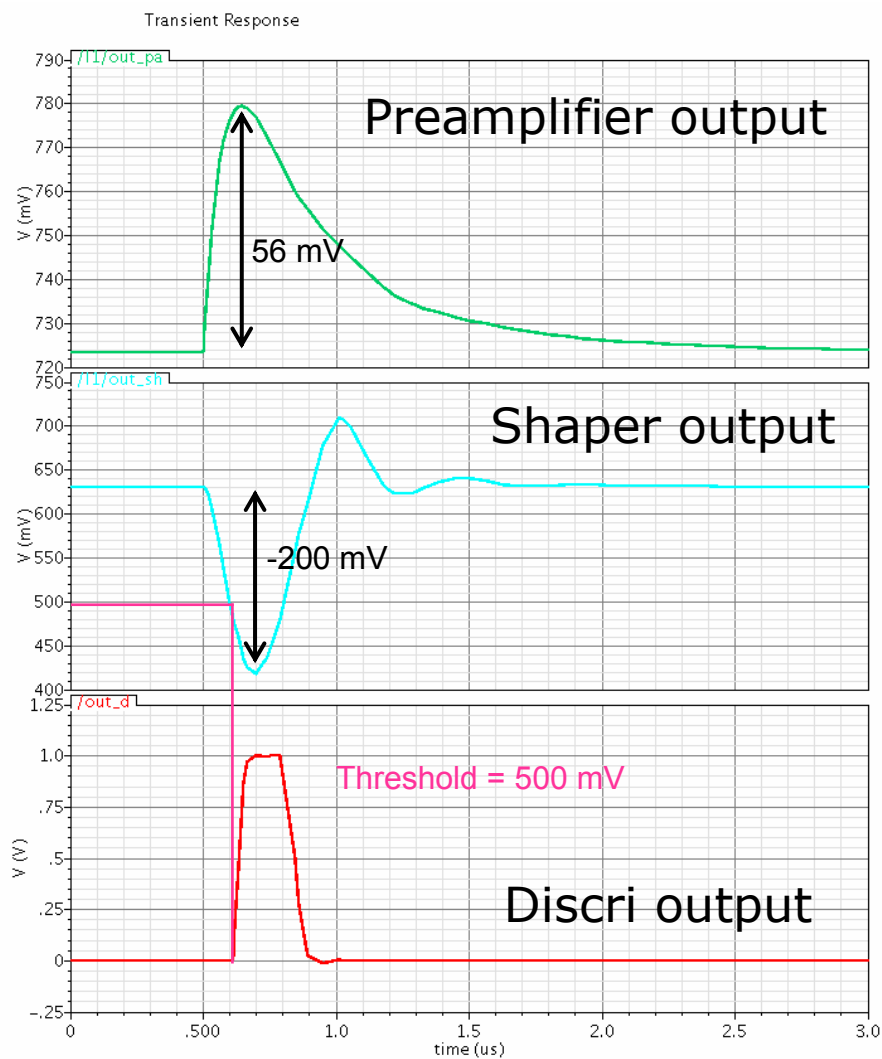
This chip will be designed with the 3D Tezzaron process with wafers from 0.13 um Chartered Semiconductor

LAL **purpose**: sub-micron readout circuit dedicated for innovative high granular planar pixel sensors for ATLAS upgrade Pixel detector

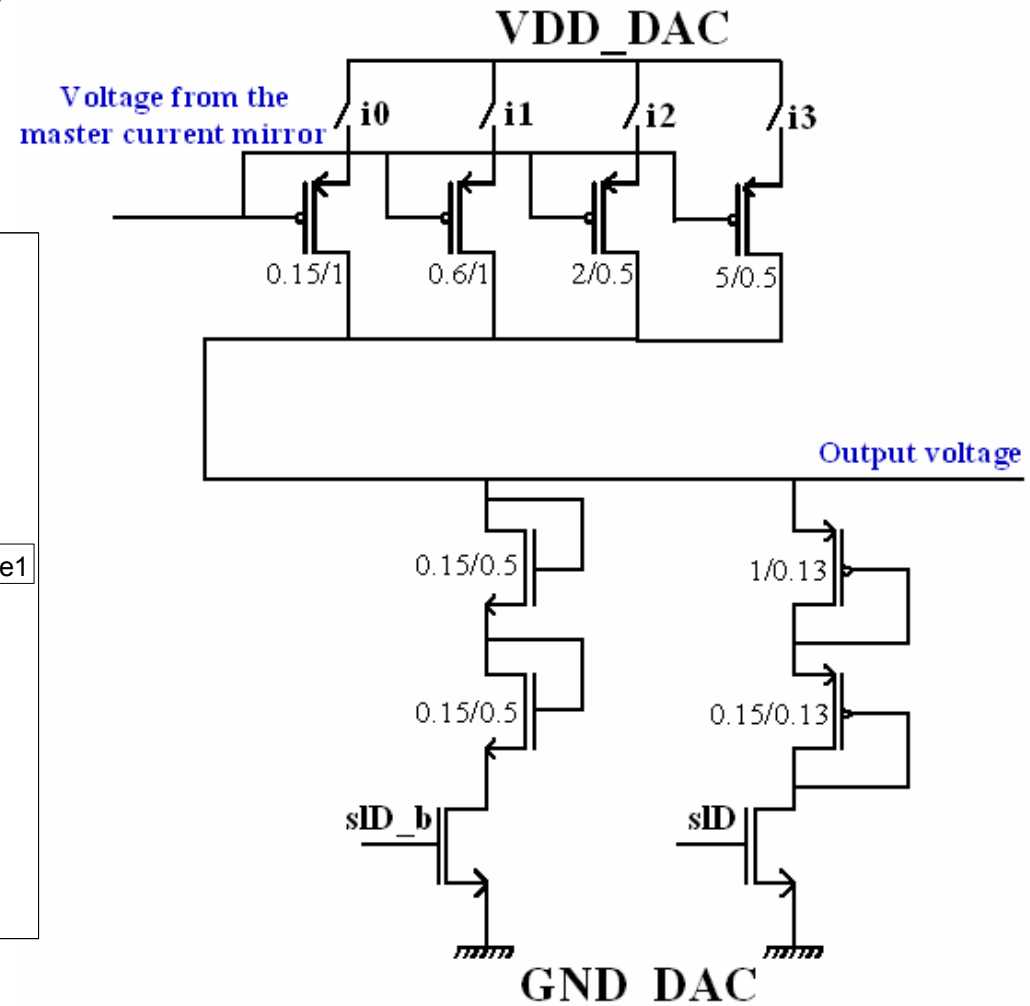
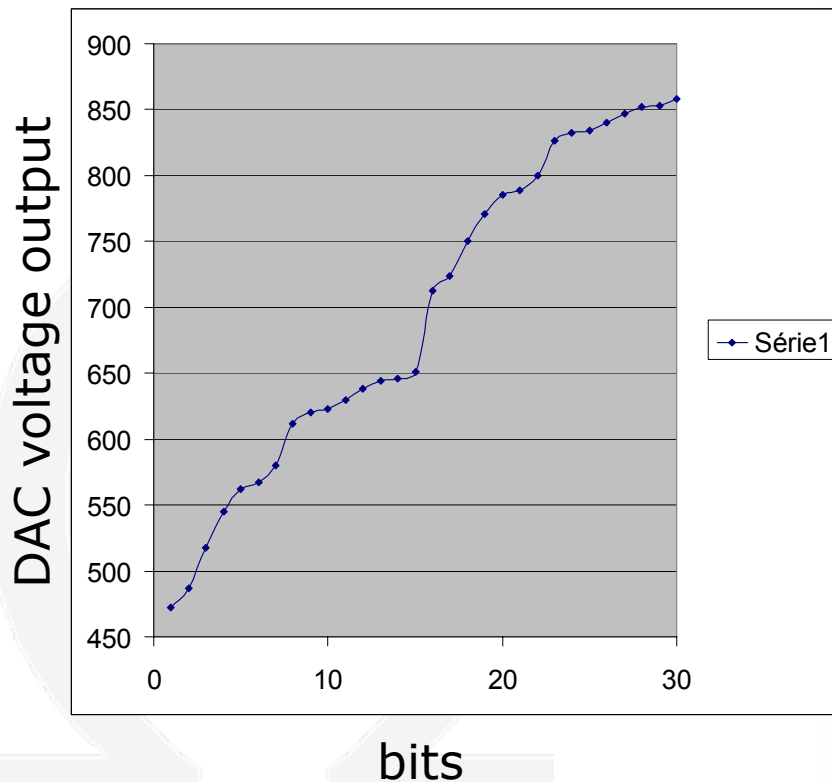
OMEGAPIX: Analogue simulation



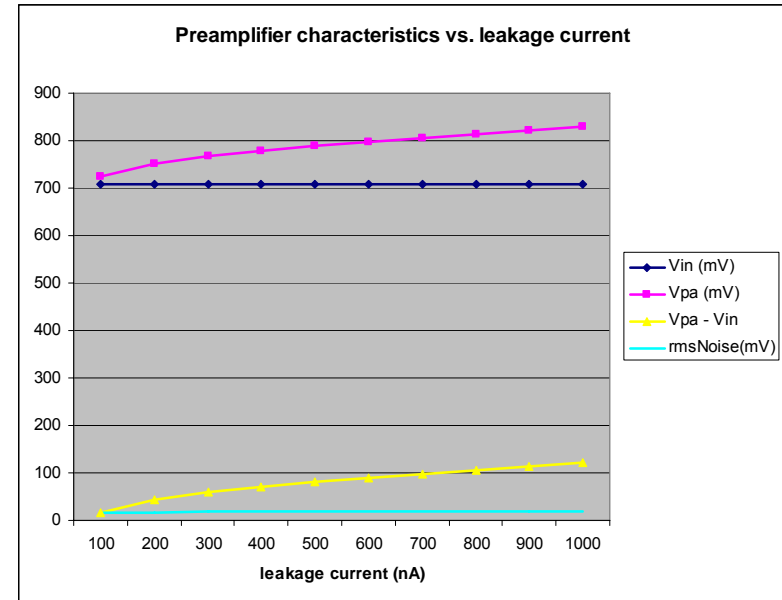
Simulation conditions: $Q_{inj} = 1000 e^-$, Shaper gain = 1000; DAC = sIDb, 0001



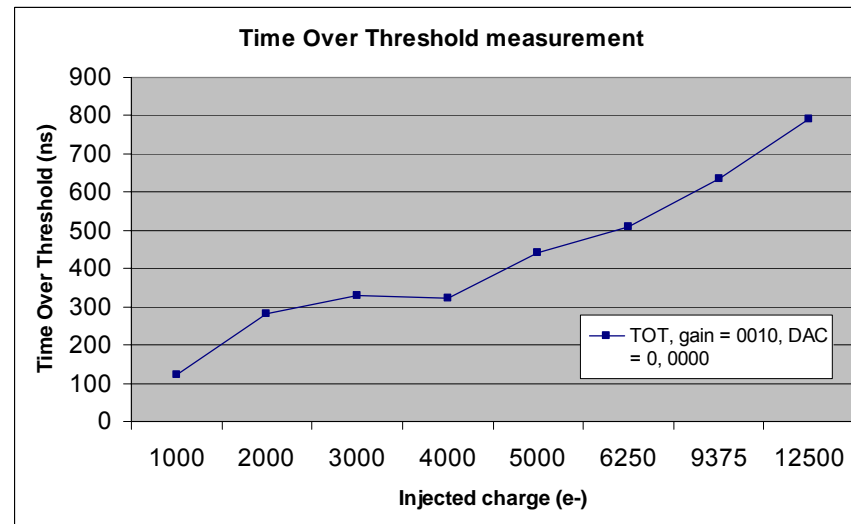
The DAC fixes the treshold voltage
In fact, only 4.5 bits



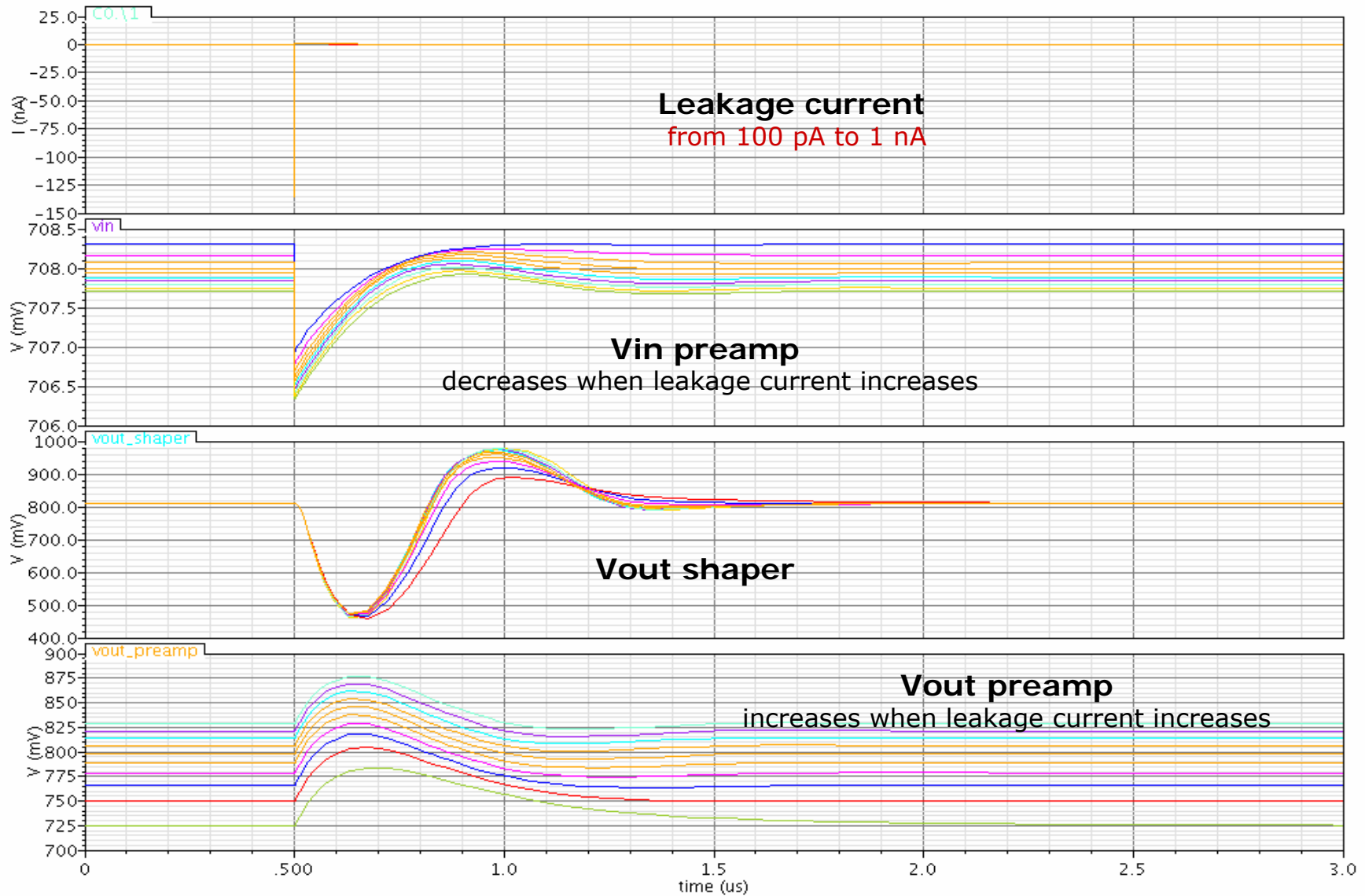
- Paraphase behavior
 - Leakage current variation when leakage current increase output preamplifier voltage increase

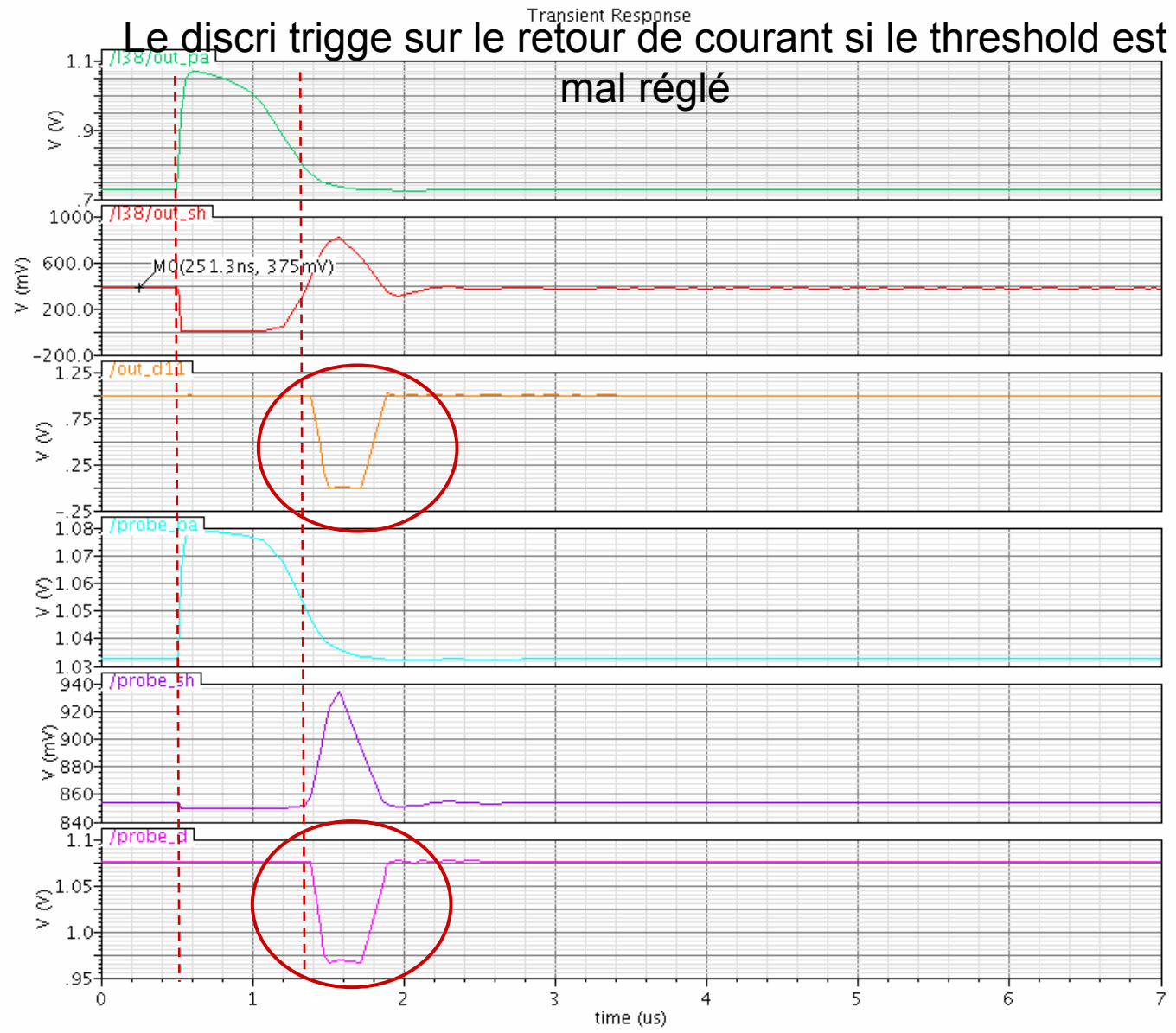


- TOT measurement not very good because of the shaper saturation

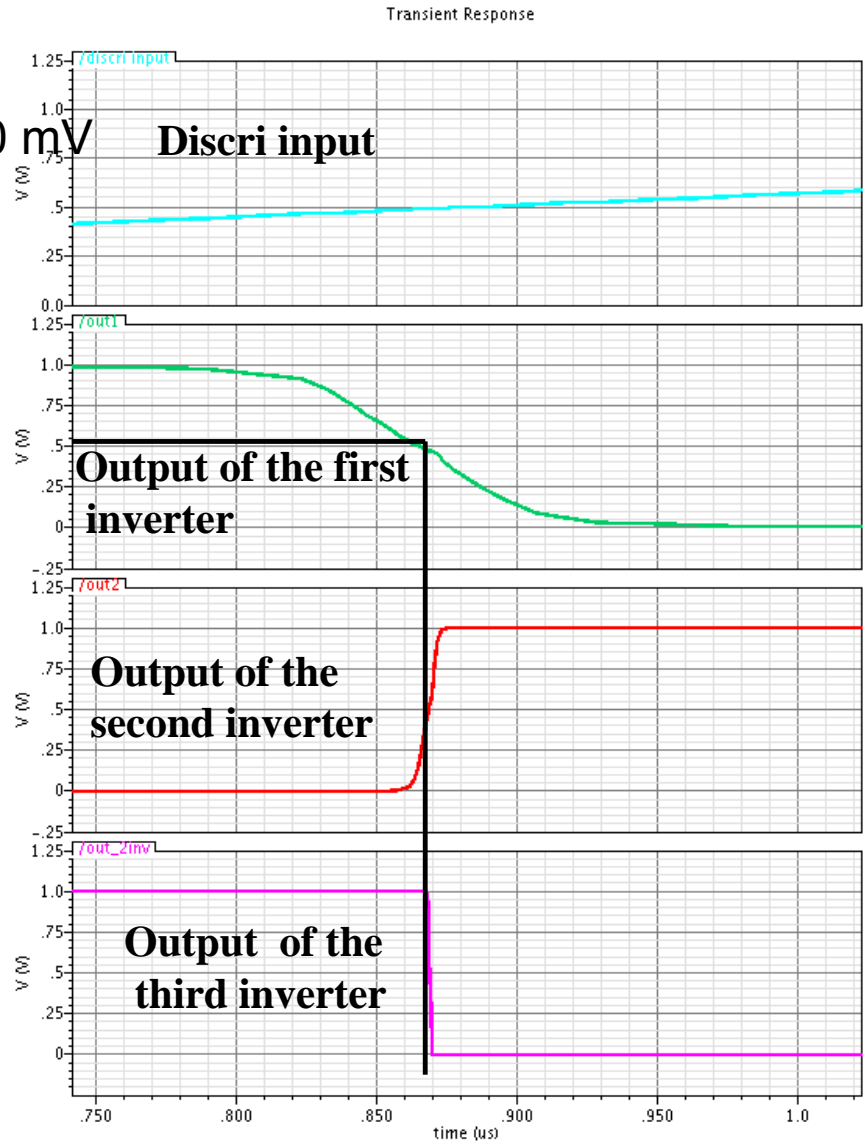


Transient Response





Intrinsèque threshold ~ 500 mV



$V_{thn} = 497 \text{ mV}$
 $V_{thp} = -470 \text{ mV}$
 $VDD = 1 \text{ V}$

Intrinsic threshold
 $= 0.5 \text{ mV}$

